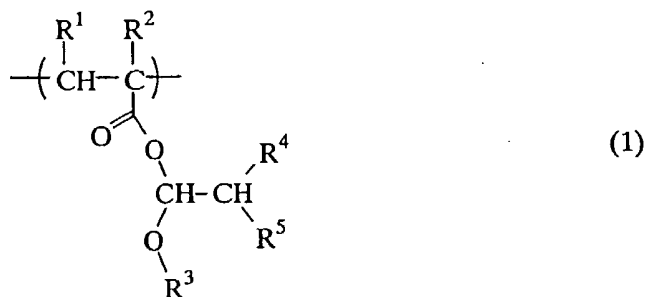


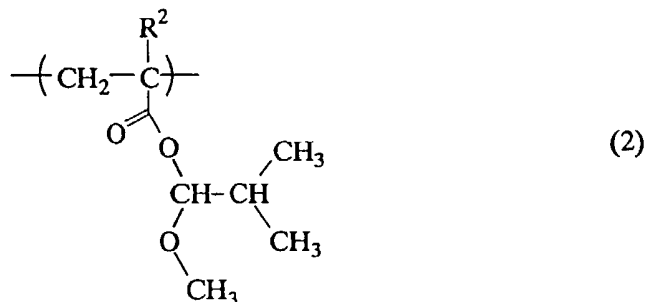
CLAIMS:

1. A resist composition comprising a polymer comprising  
 recurring units of the following general formula (1) and  
 5 having a weight average molecular weight of 1,000 to 500,000,



wherein  $\text{R}^1$  and  $\text{R}^2$  are each independently hydrogen, hydroxy, a  
 straight or branched alkyl group, halogen atom or  
 trifluoromethyl group,  $\text{R}^3$  is methyl or ethyl,  $\text{R}^4$  and  $\text{R}^5$  each  
 10 are an alkyl group having 1 to 7 carbon atoms, or  $\text{R}^4$  and  $\text{R}^5$   
 may bond together to form a cyclic structure.

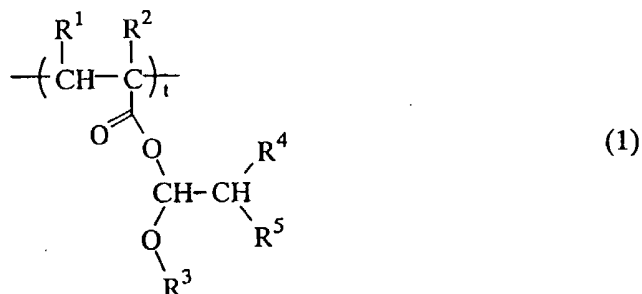
2. A resist composition comprising a polymer comprising  
 recurring units of the following general formula (2) and  
 15 having a weight average molecular weight of 1,000 to 500,000,



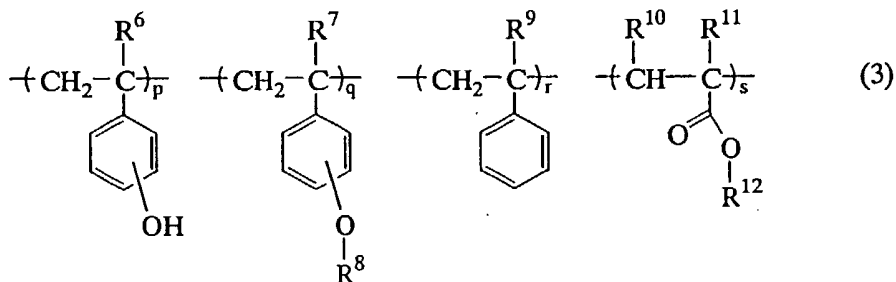
wherein  $\text{R}^2$  is hydrogen, hydroxy, a straight or branched alkyl  
 group, halogen atom or trifluoromethyl group.

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3. A resist composition comprising a polymer comprising recurring units of the following general formula (1) and recurring units of the following general formula (3) and having a weight average molecular weight of 1,000 to 500,000.

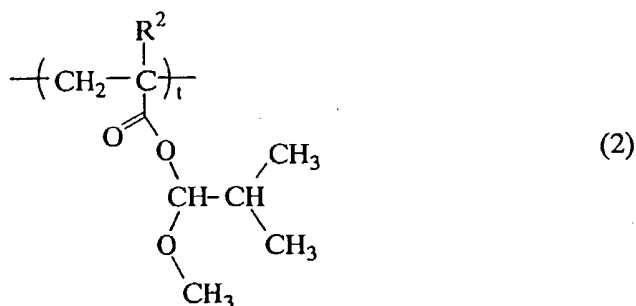


5 wherein R<sup>1</sup> and R<sup>2</sup> are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group, R<sup>3</sup> is methyl or ethyl, R<sup>4</sup> and R<sup>5</sup> each are an alkyl group having 1 to 7 carbon atoms, or R<sup>4</sup> and R<sup>5</sup> may bond together to form a cyclic structure, t is a positive number,



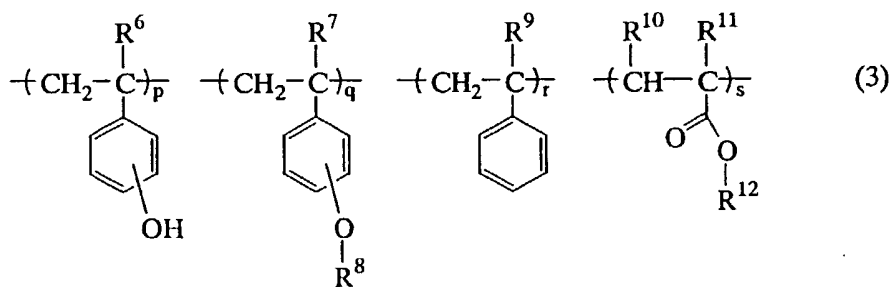
15 wherein R<sup>6</sup>, R<sup>7</sup>, R<sup>9</sup>, R<sup>10</sup> and R<sup>11</sup> are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group, R<sup>8</sup> is an alkyl group having 1 to 10 carbon atoms, R<sup>12</sup> is an alkyl group having 4 to 30 carbon atoms or silicon-substituted alkyl group, q, r and s are 0 or positive numbers, and p is a positive number.

4. A resist composition comprising a polymer comprising recurring units of the following general formula (2) and recurring units of the following general formula (3) and having a weight average molecular weight of 1,000 to 500,000,



5

wherein R<sup>2</sup> is hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group, and t is a positive number,



10 wherein R<sup>6</sup>, R<sup>7</sup>, R<sup>9</sup>, R<sup>10</sup> and R<sup>11</sup> are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group, R<sup>8</sup> is an alkyl group having 1 to 10 carbon atoms, R<sup>12</sup> is an alkyl group having 4 to 30 carbon atoms or silicon-substituted alkyl group, q, r and s are 0 or  
15 positive numbers, and p is a positive number.

5. A chemically amplified positive resist composition comprising

- 20 (A) an organic solvent,  
(B) the polymer of claim 1 as a base resin, and  
(C) a photoacid generator.

6. A chemically amplified positive resist composition comprising

- (A) an organic solvent,
- (B) the polymer of claim 1 as a base resin,
- (C) a photoacid generator, and
- (D) a dissolution inhibitor.

7. The chemically amplified positive resist composition of claim 5, further comprising (E) a basic compound.

8. A process for forming a resist pattern comprising the steps of:

applying the resist composition of claim 1 onto a substrate to form a coating,

heat treating the coating and then exposing it to high-energy radiation or electron beam through a photo mask, and

optionally heat treating the exposed coating and developing it with a developer.